

Silicon NPN Power Transistors

BUT56AF

DESCRIPTION

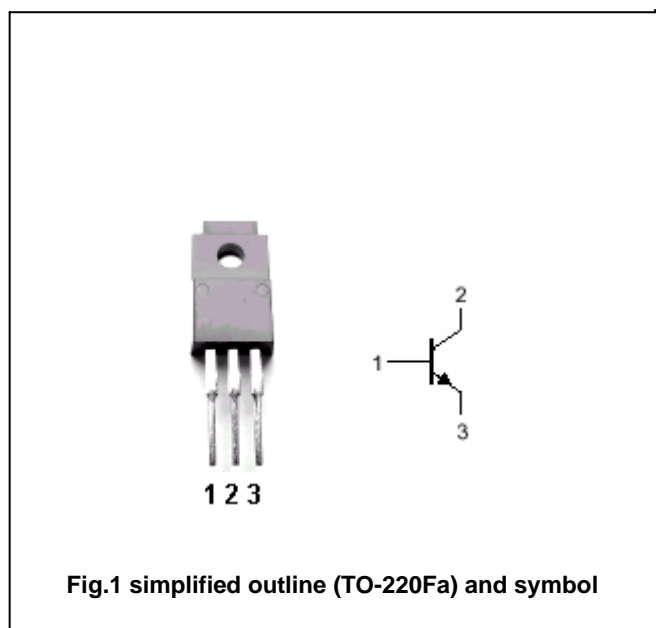
- With TO-220Fa package
- High voltage;high speed
- High power dissipation

APPLICATIONS

- Switching mode power supply

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		10	A
I_{BM}	Base current-peak		4	A
P_{tot}	Total power dissipation	$T_C=25$	50	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100mA ; L _C =125mH	450			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.8A			2.0	V
I _{CES}	Collector cut-off current	V _{CE} =1000V ; V _{BE} =0 T _j =150			1.0 2.0	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	15		45	
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =2V	4			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V ; f=1.0MHz		10		MHz

Switching times

t _{off}	Turn-off time	I _C =4A ; I _{B1} =-I _{B2} =1.25A t _p =20 μs			4	μs
t _f	Fall time				1	μs

PACKAGE OUTLINE

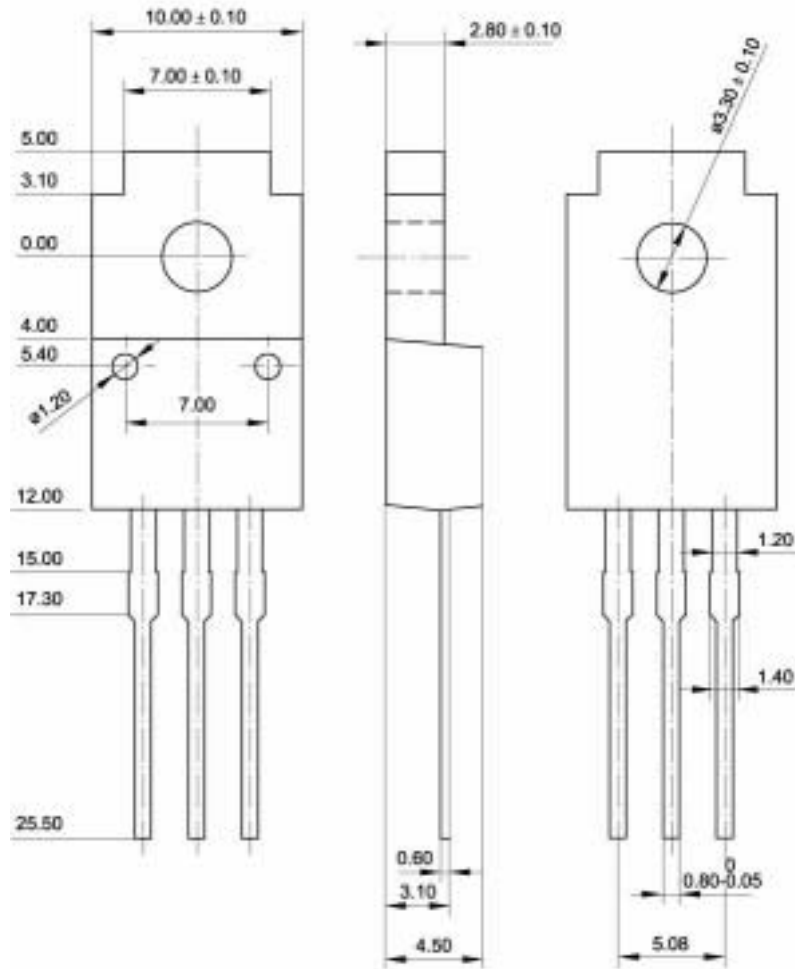


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)